

※ 考生請注意：本試題不可使用計算機。請於答案卷(卡)作答，於本試題紙上作答者，不予計分。
 註：請提供詳細推導過程，並帶入計算數字，不須算出開根號之數字。

1. (20%) Consider the circuit shown in Fig. 1 and the diodes are ideal. (a) Sketch the transfer characteristics (v_o versus v_{in}) (10%). (b) Denote the ON/OFF of diode A and diode B at each segment in (a) (5%). (c) Plot the waveforms of the input and output signals ($v_o(t)$ and $v_{in}(t)$) (5%).

2. (30%) Consider the circuit in Fig. 2. The NMOS transistor has $KP=50\mu A/V^2$, $V_{to}=1 V$, $L=5\mu m$, $W=500\mu m$ and $r_d = \infty$. (a) Determine I_{DQ} , V_{DSQ} and g_m (15%). (b) Plot the small-signal equivalent circuit for the frequency of v_{in} is in the midband range. (6%). (c) Compute the voltage gain, input resistance and output resistance (9 %).

3. (20%) Consider the circuit shown in Fig. 3. Using the summing-point constraint for both op amps to derive expressions for the voltage gains $A_1 = v_{o1}/v_{in}$ (10%) and $A_2 = v_{o2}/v_{in}$ (10%).

4. (20%) Consider the circuit shown in Fig. 4. Derive an expression for the voltage transfer ratio $A(f)$ (10%). Sketch the magnitude Bode plot to scale (10%).

5. (10%) Design a two-input CMOS NAND gate. (a) Plot the circuit diagram (5%). (b) Show the truth table and ON/OFF of the PMOS and NMOS transistors (5%).

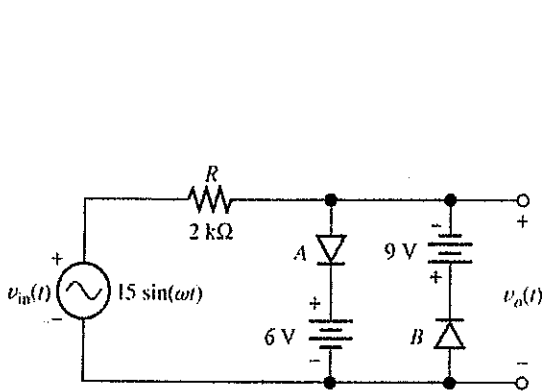


Fig. 1

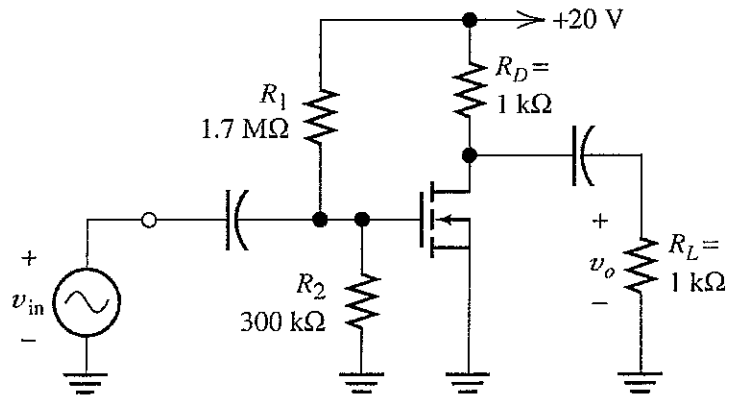


Fig. 2

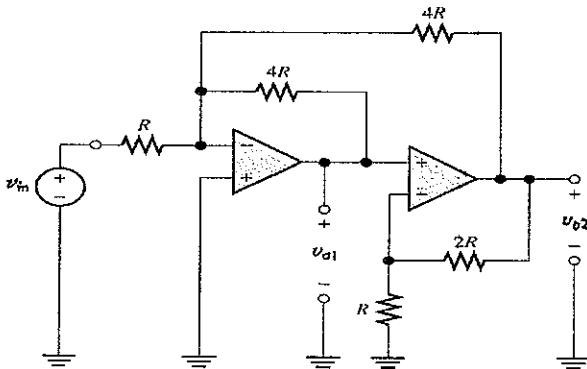


Fig. 3

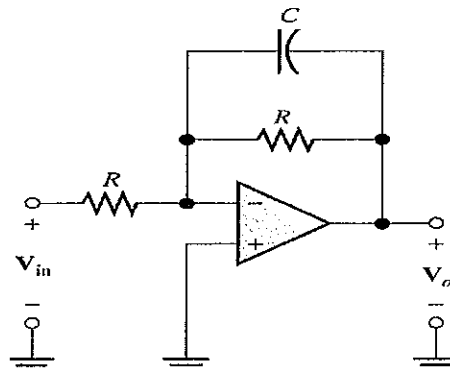


Fig. 4